

# Dual Switching Diode

## FEATURE

- We declare that the material of product compliance with RoHS requirements.

## ORDERING INFORMATION

Device	Package	Shipping
LMBD7000LT1G	SOT-23	3000/Tape & Reel
LMBD7000LT3G	SOT-23	10000/Tape & Reel

## MAXIMUM RATINGS(EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	100	Vdc
Forward Current	$I_F$	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board <sup>(1)</sup> $T_A = 25^\circ\text{C}$	$P_D$	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, <sup>(2)</sup> $T_A = 25^\circ\text{C}$	$P_D$	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	°C

## DEVICEMARKING

LMBD7000LT1G = M5C

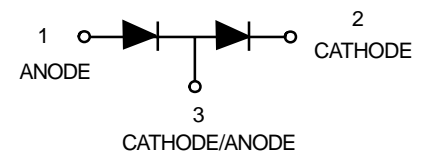
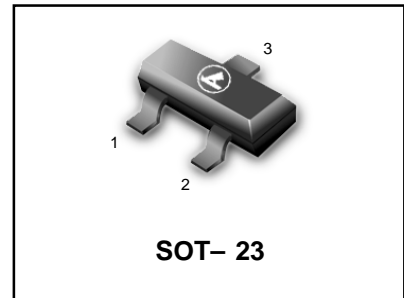
## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)(EACH DIODE)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Reverse Breakdown Voltage ( $I_{(BR)} = 100 \mu\text{Adc}$ )	$V_{(BR)}$	100	—	Vdc
Reverse Voltage Leakage Current ( $V_R = 50 \text{ Vdc}$ )	$I_R$	—	1.0	$\mu\text{Adc}$
( $V_R = 100 \text{ Vdc}$ )	$I_{R2}$	—	3.0	
( $V_R = 50 \text{ Vdc}, 125^\circ\text{C}$ )	$I_{R3}$	—	100	
Forward Voltage ( $I_F = 1.0 \text{ mAdc}$ )	$V_F$	0.55	0.7	Vdc
( $I_F = 10 \text{ mAdc}$ )		0.67	0.82	
( $I_F = 100 \text{ mAdc}$ )		0.75	1.1	
Reverse Recovery Time ( $I_F = I_R = 10 \text{ mAdc}$ ) (Figure 1)	$t_{rr}$	—	4.0	ns
Capacitance ( $V_R = 0\text{V}$ )	$C$	—	1.5	pF

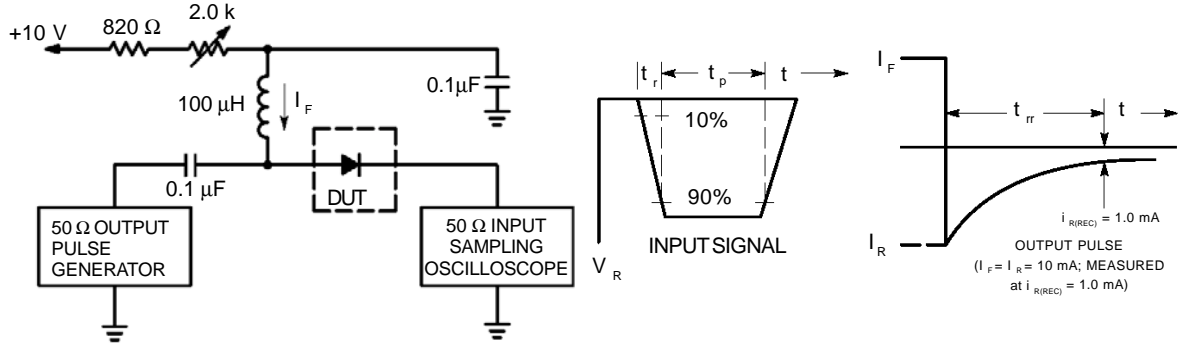
1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

## LMBD7000LT1G



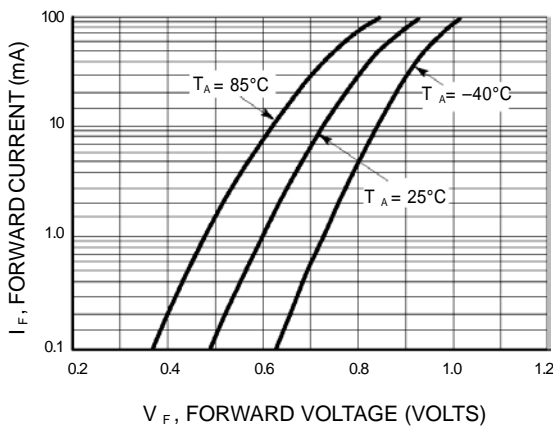
**LMBD7000LT1G**



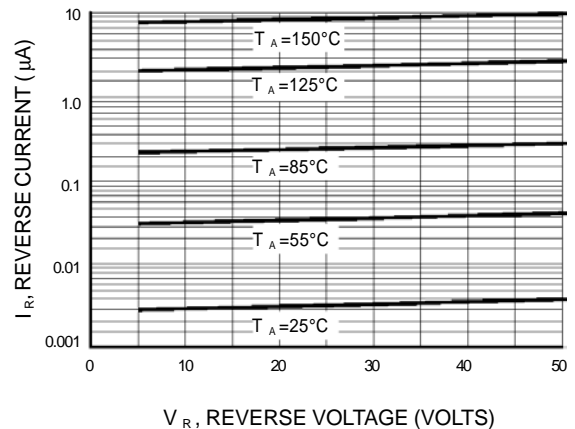
- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current ( $I_F$ ) of 10mA.
- 2. Input pulse is adjusted so  $I_{R(\text{peak})}$  is equal to 10mA.
- 3.  $t_p \gg t_{rr}$

**Figure 1. Recovery Time Equivalent Test Circuit**

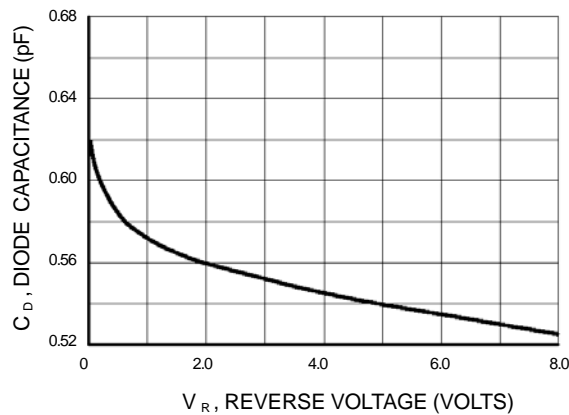
**CURVES APPLICABLE TO EACH CATHODE**



**Figure 2. Forward Voltage**



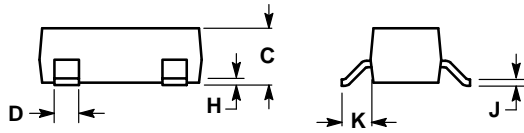
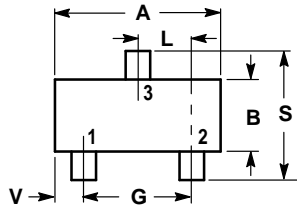
**Figure 3. Leakage Current**



**Figure 4. Capacitance**

**LMBD7000LT1G**

**SOT-23**

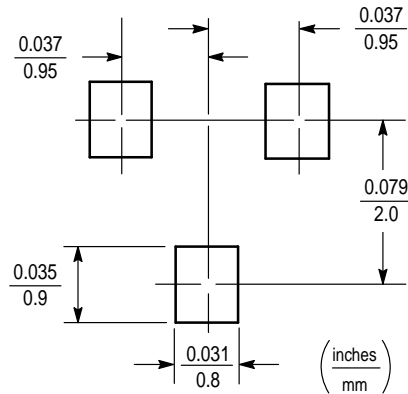


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

- PIN 1. ANODE  
 2. CATHODE  
 3. CATHODE/ANODE



## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for* [Diodes - General Purpose, Power, Switching category:](#)

*Click to view products by* [Leshan manufacturer:](#)

Other Similar products are found below :

[MMBD3004S-13-F](#) [RD0306T-H](#) [DSE010-TR-E](#) [BAV17-TR](#) [BAV19-TR](#) [1N3611](#) [NTE156A](#) [NTE574](#) [NTE6244](#) [1SS181-TP](#) [1SS193,LF](#)  
[1SS400CST2RA](#) [SDAA13](#) [SHN2D02FUTW1T1G](#) [LS4151GS08](#) [FC903-TR-E](#) [1N4449](#) [1N456A](#) [1N4934-E3/73](#) [1N914B](#) [1N914BTR](#)  
[1SS226-TP](#) [RFUH20TB3S](#) [D291S45T](#) [BAV300-TR](#) [BAW56DWQ-7-F](#) [BAW75-TAP](#) [MM230L-CAA](#) [IDW40E65D1](#) [JAN1N3600](#) [LL4151-](#)  
[GS18](#) [053684A](#) [SMMSD4148T3G](#) [707803H](#) [NSVDAN222T1G](#) [CDSZC01100-HF](#) [LL4150-M-08](#) [1N4454-TR](#) [BAV199E6433HTMA1](#)  
[BAS28-7](#) [BAW56HDW-13](#) [BAS28 TR](#) [VS-HFA04SD60STR-M3](#) [NSVM1MA152WKT1G](#) [RGP30D-E3/73](#) [BAV99TQ-13-F](#) [BAS21DWA-7](#)  
[NTE6250](#) [NTE582-4](#) [NTE582-6](#)